



### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
2014	$75m\Omega @ V_{GS} = -4.5V$	-3.2A
-20V	110mΩ @ V <sub>GS</sub> = -2.5V	-2.9A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Load Switch
- Power Management Functions
- Portable Power Adaptors

#### Features

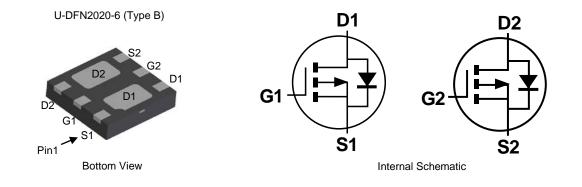
- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Maximum Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The DMP2110UFDBQ is suitable for automotive applications requiring specific change control; This part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

https://www.diodes.com/guality/product-definitions/

### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 @
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2110UFDBQ-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2110UFDBQ-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



### **Marking Information**

#### U-DFN2020-6 (Type B)



H6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020)

W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	0	1	2	3	4	5	6	7	8	9	0	1
i												
Week	1-26			27-52			53					
Code	A-Z			a-z			Z					
Internal Code	Sı	ın	Mor	n	Tue	1	Wed	Thu		Fri		Sat
Code	Т	-	U		V		W	Х		Y		7



## Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
Continuous Drain Current (Note 6) $V_{GS} = -4.5V$	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-3.2 -2.6	А
Maximum Continuous Body Diode Forward Current (I	I <sub>S</sub>	-1.05	A		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-15	A		

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	0.82	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>ƏJA</sub>	153	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	1.14	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>ÐJA</sub>	110	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

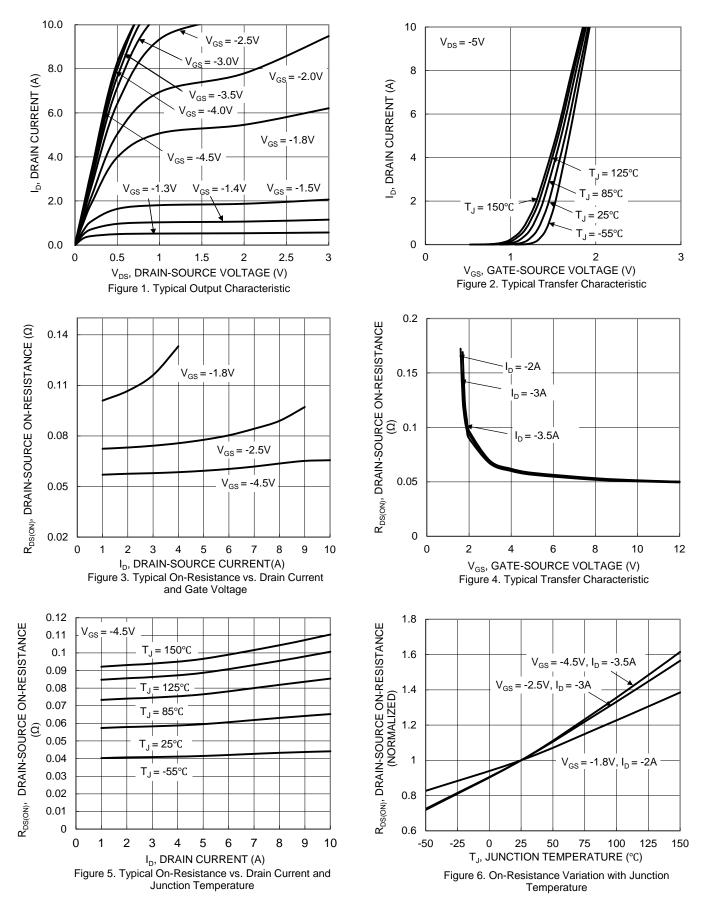
## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						-
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	—	_	-1.0	μA	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	—		±100	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.45		-1.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
		—	_	75		$V_{GS} = -4.5V, I_D = -2.8A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	110	mΩ	$V_{GS} = -2.5V, I_D = -2.0A$
		—	—	168		$V_{GS} = -1.8V, I_D = -1.0A$
Diode Forward Voltage	V <sub>SD</sub>	—		-1.0	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	—	443		pF	
Output Capacitance	Coss	—	59	—	pF	− V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, − f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	—	47	—	pF	
Total Gate Charge (V <sub>GS</sub> = -4.5V)		—	6.0	—	nC	
Total Gate Charge (V <sub>GS</sub> = -8V)	Qg	—	12.7	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	0.6	—	nC	$-V_{DS} = -4.5V, I_{D} = -3.0A$
Gate-Drain Charge	Q <sub>gd</sub>	—	1.8	_	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.0	_	ns	
Turn-On Rise Time	t <sub>R</sub>	—	3.7	—	ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V,
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	24.5	_	ns	$R_L = 10\Omega, R_g = 6\Omega$
Turn-Off Fall Time	t <sub>F</sub>	—	9.5	—	ns	1
Body Diode Reverse Recovery Time	t <sub>RR</sub>		8.3	—	ns	I <sub>S</sub> = -1.0A, dl/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	2.0	_	nC	I <sub>S</sub> = -1.0A, dl/dt = 100A/µs

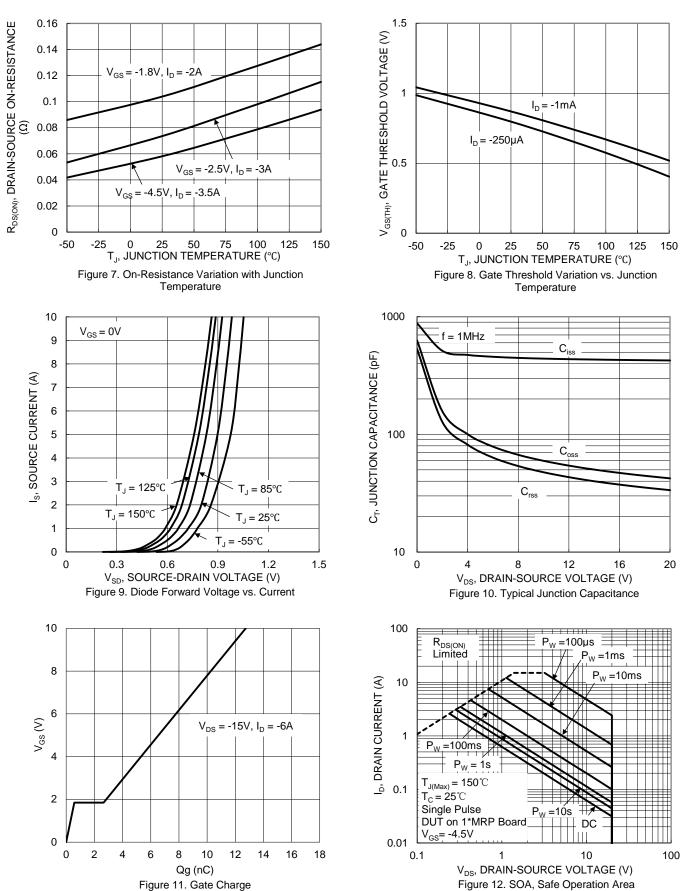
 Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:



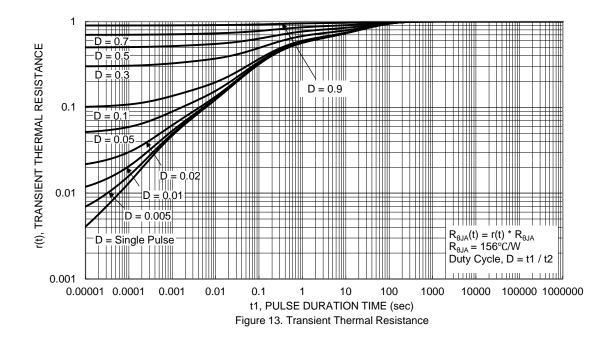
## DMP2110UFDBQ







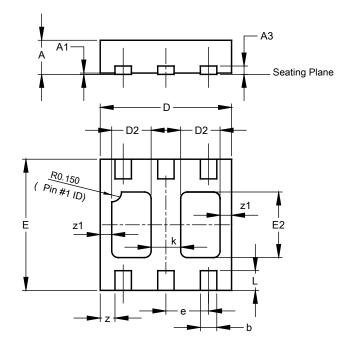






# **Package Outline Dimensions**

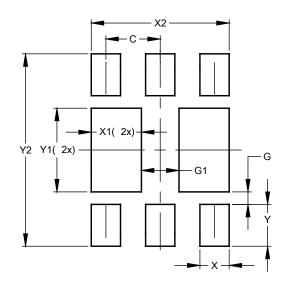
Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DFN2020-6								
	Туре В								
Dim	Min	Max	Тур						
Α	0.545	0.605	0.575						
A1	0.00	0.05	0.02						
A3	-	-	0.13						
b	0.20	0.30	0.25						
D	1.95	2.075	2.00						
D2	0.50	0.70	0.60						
е	-	-	0.65						
E	1.95	2.075	2.00						
E2	0.90	1.10	1.00						
k	-	-	0.45						
L	0.25	0.35	0.30						
z	-	-	0.225						
z1	-	-	0.175						
All	Dimens	ions in	mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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